

In the Claims:

1. (Currently Amended) A method for preventing an out-diffusion of impurities implanted in source/drain regions when forming a transistor of a semiconductor device, comprising the steps of:

forming a gate electrode on a semiconductor substrate;

ion-implanting impurities into the semiconductor substrate using the gate electrode as a mask to form source/drain junction regions ~~a source/drain junction region by~~;

forming an oxide film over the gate electrode and the source/drain regions ~~on the resulting structure~~ via one of a CVD process and a PVD process at a temperature below 700 °C so as to prevent an out-diffusion of impurities implanted in the source/drain regions toward the surface of the substrate, and if the oxide film is formed at the temperature below 600 °C, performing thermal treatment of the semiconductor substrate at a temperature ranging from 600 °C to 700°C under a nitrogen gas atmosphere; and

forming a nitride film spacer on a sidewall of the gate electrode.

2. (Original) The method according to claim 1, wherein the step of ion-implanting impurities comprises ion-implanting ^{31}P at an energy ranging from 10 to 35KeV and at a dose ranging from 1.0E12 to 5.0E13 ions/cm².

3. (Original) The method according to claim 1, wherein the step of ion-implanting process impurities comprises ion-implanting ^{75}As at an energy ranging from 15 to 70KeV and at a dose ranging from 1.0E12 to 5.0E13 ions/cm².

4. (Original) The method according to claim 1, wherein the ion-implanting process is performed using a single-type equipment without wafer tilt and rotation.

5. (Currently Amended) The method according to claim 1, wherein the ion-implanting process is performed with a tilt of 1° and in a bi-rotation or a ~~quadruple~~ quadruple rotation configuration using a single-type equipment.

Claims 6-7 (Canceled).

8. (Currently Amended) The method according to ~~claim 7~~ claim 1, wherein the thermal treatment is a rapid thermal treatment performed for 1 to 5 minutes or a thermal treatment performed in a furnace for a time period ranging from 1 minutes to 6 hours.

9. (Currently Amended) The method according to ~~claim 7~~ claim 1, wherein the thermal treatment is in a furnace for 1 minute to 6 hours.